

VS-20CTH03SPbF, VS-20CTH03-1PbF

Vishay Semiconductors

RoHS

COMPLIANT

HALOGEN

FREE

Hyperfast Rectifier, 2 x 10 A FRED Pt®

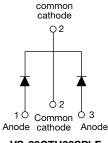


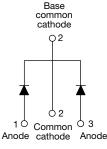


TO-263AB (D²PAK)

Base

TO-262AA





VS-20CTH03SPbF

VS-20CTH03-1PbF

PRODUCT SUMMARY	
Package	TO-263AB (D ² PAK), TO-262AA
I _{F(AV)}	2 x 10 A
V_{R}	300 V
V _F at I _F	0.85 V
t _{rr} max.	35 ns
T _J max.	175 °C
Diode variation	Common cathode

FEATURES

- · Hyperfast recovery time
- · Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C







Vishay Semiconductors 300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Peak repetitive reverse voltage		V_{RRM}		300	V	
Average rectified forward current	per diode		T _C = 160 °C	10		
Average rectified forward current —	per device	I _{F(AV)}		20	Α	
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C	120		
Operating junction and storage temp	eratures	T _J , T _{Stg}		-65 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	300	-	-		
Forward voltage	M	I _F = 10 A	-	1.05	1.25	V	
	V _F	I _F = 10 A, T _J = 125 °C	-	0.85	0.95		
Reverse leakage current		$V_R = V_R$ rated	-	-	20		
neverse leakage current	I _R	T _J = 125 °C, V _R = V _R rated	-	6	200	μΑ	
Junction capacitance	C _T	$V_{R} = 300 \text{ V}$	-	30	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	



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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt =$	50 A/μs, V _R = 30 V	-	-	35	
Payaraa raaayany tima		$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	-	30	no
Reverse recovery time	t _{rr}	T _J = 25 °C	$I_F = 10 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	31	-	ns
		T _J = 125 °C		-	42	-	
Dools was a surveyed		T _J = 25 °C		-	2.4	-	^
Peak recovery current	I _{RRM}	T _J = 125 °C		-	5.6	-	A
Reverse recovery charge	0	T _J = 25 °C		-	36	-	nC
	Q _{rr}	T _J = 125 °C		-	120	-	1110

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per diode	R _{thJC}		-	-	1.5	°C/W
Weight			-	2.0	-	g
vveignt			-	0.07	-	oz.
Mounting torque			6.0	_	12	kgf · cm
Wounting torque			(5.0)		(10)	(lbf · in)
Marking device		Case style TO-263AB (D ² PAK)		20CT	H03S	
Iviai kii ig device		Case style TO-262AA	20CTH03-1			



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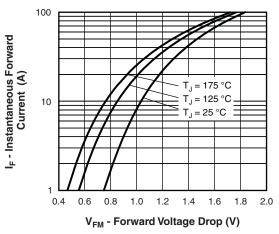


Fig. 1 - Maximum Forward Voltage Drop Characteristics

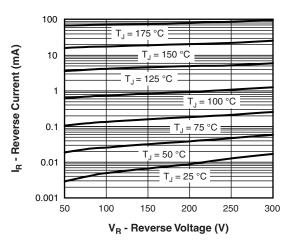


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

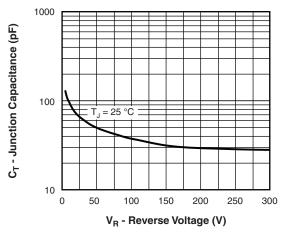


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

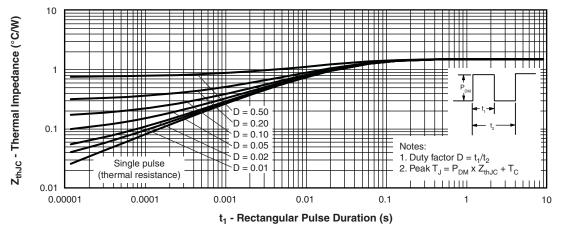


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

100

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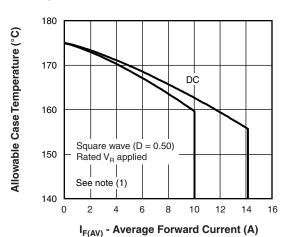


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

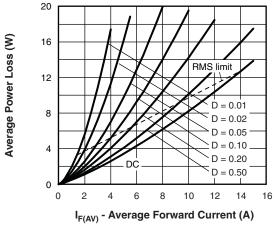


Fig. 6 - Forward Power Loss Characteristics

I_F = 10 A $T_J = 125~^{\circ}C$ t_{rr} (ns) T_J = 25 °C V_R = 200 V 10 1000 dl_F/dt (A/μs)

Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

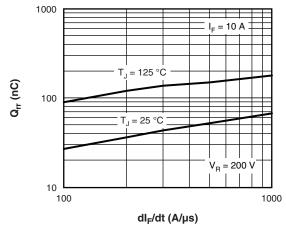


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = Inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = Rated V_R

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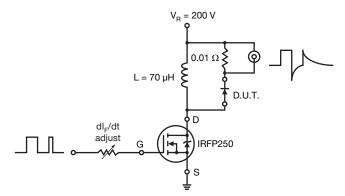
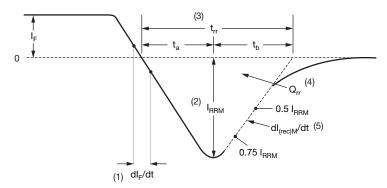


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dI_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

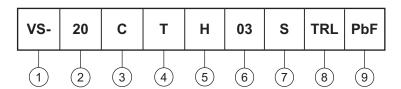
Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



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Current rating (20 A)

C = common cathode

T = TO-220, D^2PAK

3 4 5 H = hyperfast rectifier

Voltage rating (03 = 300 V)

• $S = D^2PAK$

• -1 = TO-262

8 • None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D²PAK package)

• TRR = tape and reel (right oriented, for D²PAK package)

9 PbF = lead (Pb)-free

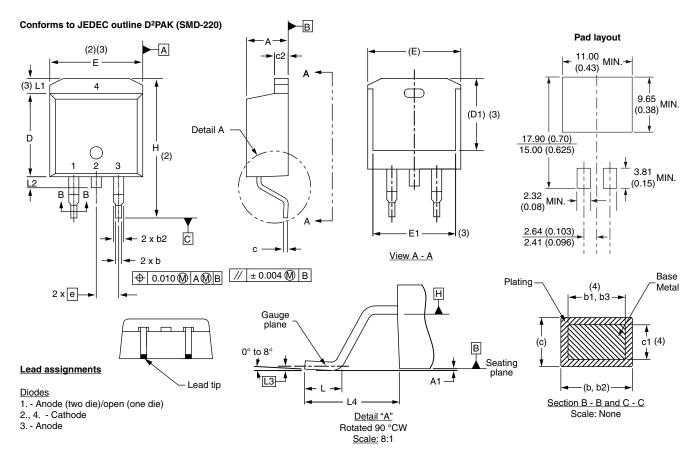
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95014					
Part marking information	www.vishay.com/doc?95008					
Packaging information	www.vishay.com/doc?95032					



Vishay High Power Products

D²PAK, TO-262

DIMENSIONS FOR D²PAK in millimeters and inches



SYMBOL	MILLIN	IETERS	INCHES		NOTES	
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INC	HES	NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}\,$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch

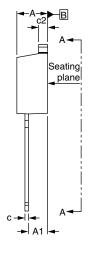
(7) Outline conforms to JEDEC outline TO-263AB

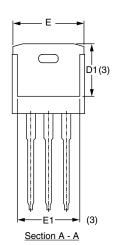
Vishay High Power Products

D²PAK, TO-262



DIMENSIONS FOR TO-262 in millimeters and inches





⊕ 0.010**⋒**|A**⋒**|B

Lead assignments

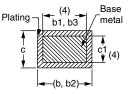


Diodes

-3 x b2 --3 x b

> 1. - Anode (two die)/open (one die) 2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIM	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
Е	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54	BSC	0.100) BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



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